



《风光欣》技术资料

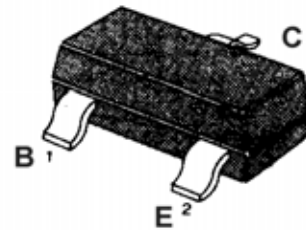
MMBT6427

NPN EPITAXIAL SILICON TRANSISTOR

ABSOLUTE MAXIMUM RATINGS(TA=25)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	40	V
Collector-Emitter Voltage	V _{CEO}	30	V
Emitter -Base Voltage	V _{EBO}	5	V
Collector Current	I _c	500	mA
Collector Dissipation	P _c	200	mW
Junction Temperature	T _j	150	
Storage Temperature	T _{STG}	-55 ~150	

SOT-23



ELECTRICAL CHARACTERISTICS (TA=25)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV _{CB0}	I _c = 100 μ A, I _E =0	40			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _c = 2mA, I _B =0	32			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E = 100 μ A, I _c =0	5			V
Collector Cut-off Current	I _{CB0}	V _{CB} = 40V, I _E =0			100	nA
Emitter Cut-off Current	I _{EBO}	V _{EB} = 6V, I _c =0			100	nA
DC Current Gain	H _{FE}	V _{CE} = 5V, I _c = 10mA	10000		100000	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _c = 500mA, I _B = 50mA		0.28	1.2	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _c = 500mA, I _B = 50mA		0.98	1.2	V
Transition Frequency	f _T	V _{CE} = 10V, I _c = 50mA		100		MHz
Collector Output Capacitance	C _{ob} f=1MHz	V _{CB} = 10V, I _E = 0		9		pF